

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 05-074724
(43)Date of publication of application : 26.03.1993

(51)Int.Cl. H01L 21/205
H01L 21/365

(21)Application number : 03-233107 (71)Applicant : TOPPAN PRINTING CO LTD
KUKIMOTO HIROSHI

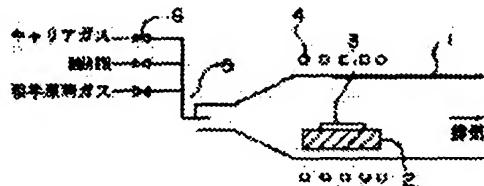
(22)Date of filing : 12.09.1991 (72)Inventor : KUKIMOTO HIROSHI
YOSHINO JUNJI
ISHIZAKI MAMORU
KANO NOBUO

(54) METHOD FOR GROWTH OF ATOMIC LAYER OF ALUMINUM COMPOUND

(57)Abstract:

PURPOSE: To widen the self-stopping condition of Al on one-atomic layer or two-atomic layers by using hydrogenated alkyl aluminum as the raw gas of aluminum.

CONSTITUTION: A supporting member 2 is arranged in a reaction container 1, and a substrate 3 is placed thereon. The substrate 3 is heated up to the prescribed temperature by the heating device 4 provided on the outer circumference of the reaction container 1. Carrier gas and the opposite raw gas, consisting of hydrogenated alkyl aluminum A R_mH_n (R is an alkyl radical, m and n indicate 1 and 2, and their sum is 3) as aluminum raw material, are introduced into the reaction container 1 by the valve 6 provided on an introducing tube 5, and the gases are fed on the substrate 3 which is heated up to the prescribed temperature. When the aluminum is used as above, the condition of gas which is hardly decomposed in the vapor phase and easily reflected on the surface is satisfied, and the self-stopping of growth under a wide growth condition can be realized.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of lodging appeal against examiner's decision of rejection]

[Date of extinction of right]